

INFORMATION DISCLOSURE CITATION

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ATTY DOCKET NO.

08228.021001

SERIAL NO.

Shiro SAKAI

FILING

March 6, 2002

GROUP

J1046 U.S. PT

10/092231

03/06/02

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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JN	A1	6,030,848	02/29/2000	Yuge et al.	438	46	04/16/1997
	A2	5,929,466	07/27/1999	Ohba et al.	257	103	06/13/1997
	A3	5,900,650	05/04/1999	Nitta	257	94	07/02/1997
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
JN	A6	10-312971	11/24/1998	Japan	H01L	21/205		✓
	A7	2000-21789	01/21/2000	Japan	H01L	21/205		✓
	A8	11-354839	12/24/1999	Japan	H01L	33/00		✓
	A9	11-354840	12/24/1999	Japan	H01L	33/00		✓
	A10	11-354842	12/24/1999	Japan	H01L	33/00		✓

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JN	A11	English/Japanese Notice of Grounds For Rejection, Japanese Patent Application Serial No. 2000-227963, 7 pages					
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
JN	C1	11-145516	05/28/1999	Japan	H01L	33/00		✓
I	C2	11-346032	12/14/1999	Japan	H01S	3/18		✓
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	C4	2000-91252	03/31/2000	Japan	H01L	21/205		✓
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							YES	NO
JN	D1	2000-357820	12/26/2000	Japan	H01L	33/00		✓
	D2	4-297023	10/21/1992	Japan	H01L	21/205		✓
	D3	EP 0 497 350 B2	08/05/1992	Europe	C30B	25/02		

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JN	D4	Patent Abstract of Japanese Patent No. JP11354842, published 12/24/1999, 1 page						
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P09C/REV03

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PAGE 5 OF 7

INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

08228.021001

Application Number

Applicant(s)

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Group Art Unit

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"Growth of high-quality GaN by low-pressure metal-organic vapour phase epitaxy (LP-MOVPE) from 3D islands and lateral overgrowth", H. Lahreche et al.
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S. Haffouz et al.
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G3

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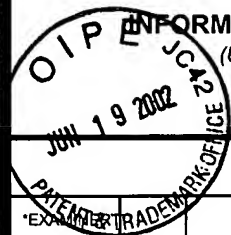
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GROUP

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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JN	A1	5,332,697	07/26/1994	Smith et al.	437	242	10/16/1991
I	A2	6,090,666	07/18/2000	Ueda et al.	438	257	09/30/1998

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	A5	11-111867	04/23/1999	Japan	H01L	21/8247		

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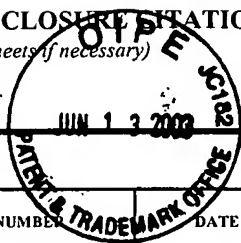
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							YES	NO
JN	A1	4-288871	08/03/1993	Japan	HO1L	21/469		✓
	A2	9-17975	01/17/1997	Japan	HO1L	27/108		✓
	A3	10-163525	06/19/1998	Japan	HO1L	33/00		✓
	A4	EP 0 961 328 A2	12/01/1999	Europe	HO1L	33/00		

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JN	A5	Japanese Patent Application Serial No. 091100294 Office Action dated March 14, 2003.
	A6	Japanese Patent Application Serial No. 2000-289103 Office Action dated April 22, 2003.

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